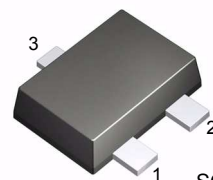


## FJZ733

### Low Frequency Amplifier

- Collector-Base Voltage :  $V_{CBO} = -60V$
- Complement to FJZ945



SOT-623F

1. Base 2. Emitter 3. Collector

### PNP Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_a = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current	-150	mA
$P_C$	Collector Power Dissipation	100	mW
$T_J$	Junction Temperature	150	$^\circ C$
$T_{STG}$	Storage Temperature	-55 ~ 150	$^\circ C$

#### Electrical Characteristics $T_a = 25^\circ C$ unless otherwise noted

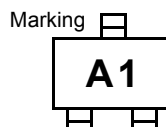
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -100\mu A, I_E = 0$	-60			V
$BV_{CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10mA, I_B = 0$	-50			V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-5			V
$I_{CBO}$	Collector Cut-off Current	$V_{CB} = -60V, I_E = 0$			-100	nA
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -5V, I_C = 0$			-100	nA
$h_{FE}$	DC Current Gain	$V_{CE} = -6V, I_C = -1mA$	40		700	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -100mA, I_B = -10mA$		-0.18	-0.3	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = -6V, I_C = -1mA$	-0.50	-0.62	-0.80	V
$f_T$	Current Gain Bandwidth Product	$V_{CE} = -6V, I_C = -10mA$	50	180		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -10V, I_E = 0, f = 1MHz$		2.8		pF
NF	Noise Figure	$V_{CE} = -6V, I_C = -0.3mA, f = 1MHz, R_s = 10k\Omega$		6.0		dB

#### Thermal Characteristics $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	1250	$^\circ C/W$

#### $h_{FE}$ Classification & Marking

Classification	R	O	Y	G	L
$h_{FE}$	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400	350 ~ 700
Marking	A2	A3	A1	A4	A5



# Typical Characteristics

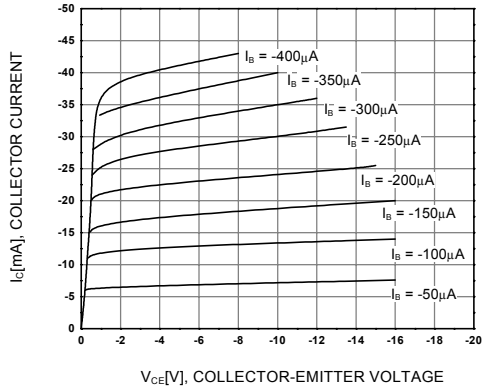


Figure 1. Static Characteristic

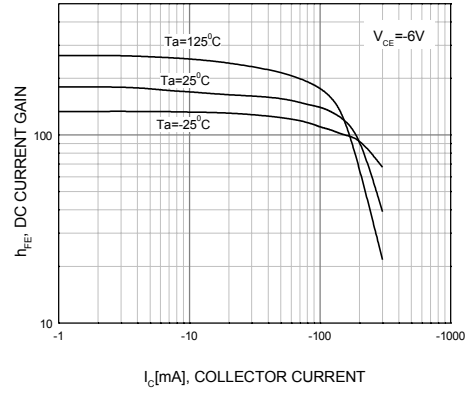


Figure 2. DC Current Gain

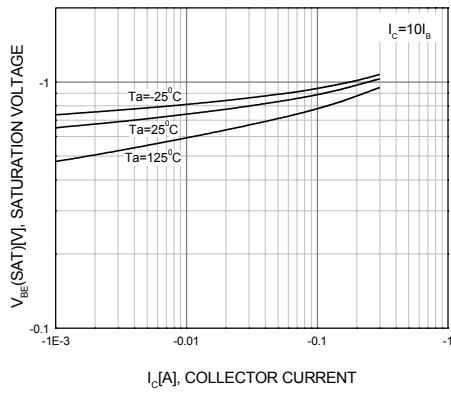


Figure 3. Base-Emitter Saturation Voltage

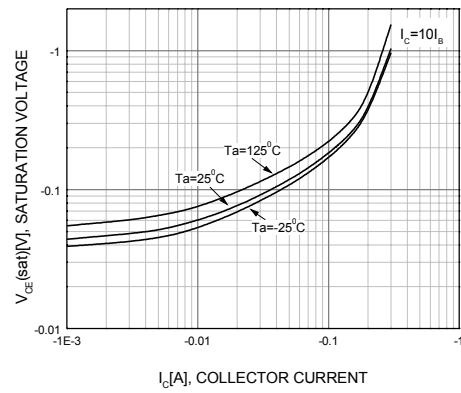


Figure 4. Collector-Emitter Saturation Voltage

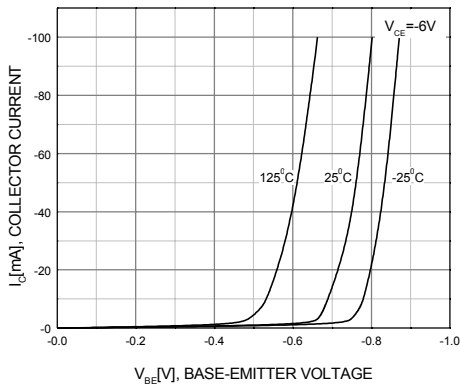


Figure 5. Base-Emitter On Voltage

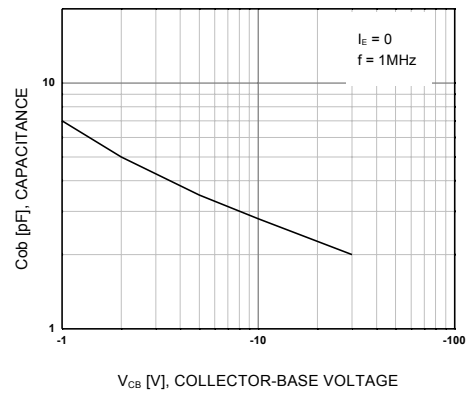


Figure 6. Collector Output Capacitance

Typical Characteristics (Continued)

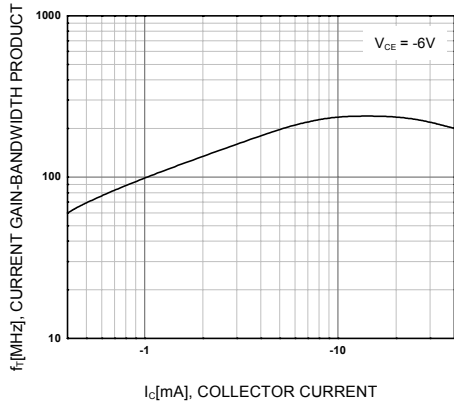
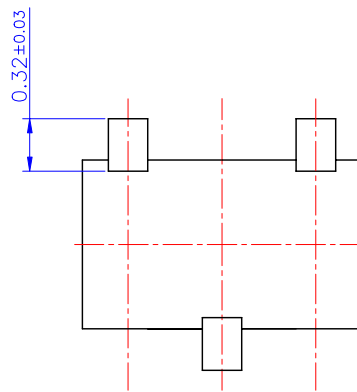
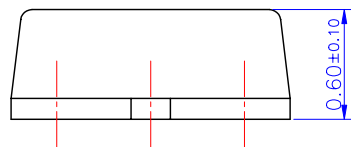
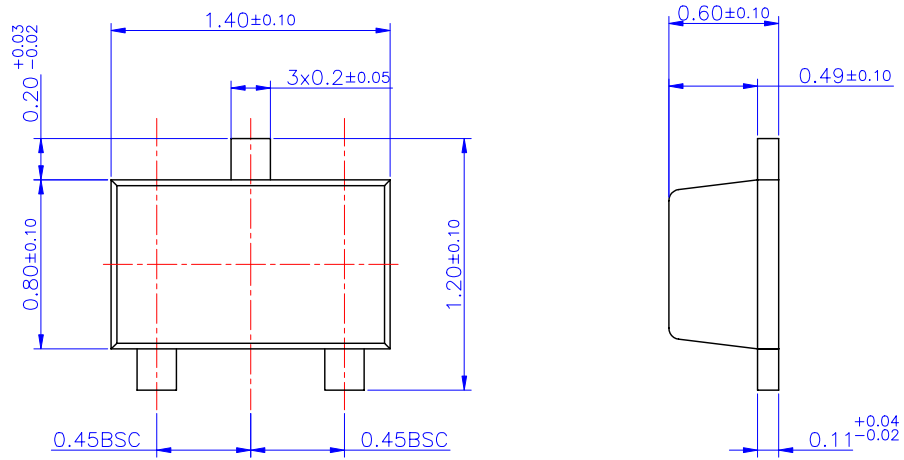


Figure 7. Current Gain Bandwidth Product

Package Dimensions

SOT-623F



Dimensions in Millimeters

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